## Daniel S Schulman

List of Publications by Year in descending order

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DANIEL S SCHULMAN

#	Article	IF	CITATIONS
1	Contact engineering for 2D materials and devices. Chemical Society Reviews, 2018, 47, 3037-3058.	38.1	561
2	Mimicking Neurotransmitter Release in Chemical Synapses <i>via</i> Hysteresis Engineering in MoS <sub>2</sub> Transistors. ACS Nano, 2017, 11, 3110-3118.	14.6	217
3	Carbon doping of WS <sub>2</sub> monolayers: Bandgap reduction and p-type doping transport. Science Advances, 2019, 5, eaav5003.	10.3	119
4	Defect-Controlled Nucleation and Orientation of WSe <sub>2</sub> on hBN: A Route to Single-Crystal Epitaxial Monolayers. ACS Nano, 2019, 13, 3341-3352.	14.6	107
5	Defect Dynamics in 2-D MoS <sub>2</sub> Probed by Using Machine Learning, Atomistic Simulations, and High-Resolution Microscopy. ACS Nano, 2018, 12, 8006-8016.	14.6	72
6	Mobility Deception in Nanoscale Transistors: An Untold Contact Story. Advanced Materials, 2019, 31, e1806020.	21.0	51
7	Thickness Trends of Electron and Hole Conduction and Contact Carrier Injection in Surface Charge Transfer Doped 2D Field Effect Transistors. ACS Nano, 2020, 14, 13557-13568.	14.6	35
8	The Prospect of Two-Dimensional Heterostructures: A Review of Recent Breakthroughs. IEEE Nanotechnology Magazine, 2017, 11, 6-17.	1.3	27
9	Superior Electro-Oxidation and Corrosion Resistance of Monolayer Transition Metal Disulfides. ACS Applied Materials & Interfaces, 2018, 10, 4285-4294.	8.0	23
10	Facile Electrochemical Synthesis of 2D Monolayers for High-Performance Thin-Film Transistors. ACS Applied Materials & Interfaces, 2017, 9, 44617-44624.	8.0	22
11	Anomalous Corrosion of Bulk Transition Metal Diselenides Leading to Stable Monolayers. ACS Applied Materials & Interfaces, 2017, 9, 39059-39068.	8.0	11
12	Three-Dimensional Integrated X-ray Diffraction Imaging of a Native Strain in Multi-Layered WSe <sub>2</sub> . Nano Letters, 2018, 18, 1993-2000.	9.1	9
13	2-D Strain FET (2D-SFET) Based SRAMs—Part I: Device-Circuit Interactions. IEEE Transactions on Electron Devices, 2020, 67, 4866-4874.	3.0	5
14	Titanium dioxide nanowire sensor array integration on CMOS platform using deterministic assembly. Nanotechnology, 2017, 28, 265501.	2.6	3
15	Steep slope 2D strain field effect transistor: 2D-SFET. , 2018, , .		3
16	Polarization-induced Strain-coupled TMD FETs (PS FETs) for Non-Volatile Memory Applications. , 2020, ,		3
17	2D Strain FET (2D-SFET)-Based SRAMs—Part II: Back Voltage-Enabled Designs. IEEE Transactions on Electron Devices, 2020, 67, 4875-4883.	3.0	3